SP00R6

0.2pF, 12KV Diode, Low Voltage Low Capacitance ESD Protection





Note: This package image is for example and reference only. for detail package drawing, please refer to the package section in this datasheet.

Description

The SP00R6 features extremely low breakdown/turn on voltages, making them more ideal protectors of low voltage -0.3 to +0.3V data lines. These robust diodes can safely absorb repetitive ESD strikes above the maximum level specified in IEC 61000-4-2 international standard (Level 4, ± 8 kV contact discharge) without performance degradation.

Pinout



Features

- ESD, IEC 61000-4-2, ±12 contact, ±15kV air
- EFT, IEC 61000-4-4, 30A (5/50ns)
- Surge Tolerance, IEC 61000-4-5 2nd Edition, 3A (8/20us)
- Low capacitance of 0.2pF (TYP)
- Space efficient 0201 package
- Halogen-free, lead-free and RoHS-compliant

Functional Block Diagram



Applications

- USB 3.x
- Thunderbolt 4 or 3
- USB4(TM)
- USB 3.2 Gen 2x2
- USB 3.2 Gen 2
- PCI Express 6.0

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.



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Absolute Maximum Ratings

Symbol	Parameter	Value	Units
l _{PP}	Peak Current (t _p =8/20µs)	3	А
T_OP	Operating Temperature	-40 to 125	°C
T _{STOR}	Storage Temperature	-55 to 150	°C

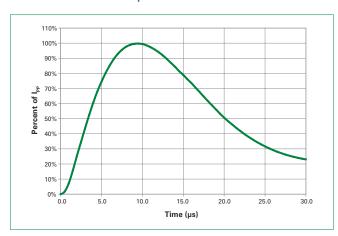
CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Characteristics (T_{OP}=25°C)

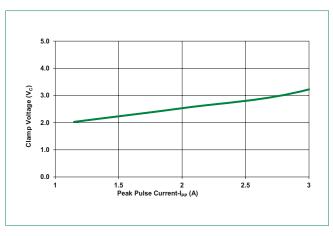
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V _{RWM}				0.3	V
Breakdown Voltage	V _{BR}	I _R =1mA	0.7		0.9	V
Reverse Leakage Current	I _{LEAK}	V_R =0.3V, Any I/O to GND			100	nA
Clamp Voltage ¹	\/	$I_{pp} = 1A, t_p = 8/20 \mu s$		2.0		V
	V _C	$I_{pp} = 2A$, $t_p = 8/20 \mu s$		2.5		V
Dynamic Resistance ³	R _{DYN}	TLP, t _p =100ns		0.3		Ω
ESD Withstand Voltage ¹	\/	IEC 61000-4-2 (Contact Discharge)	±12			kV
	V _{ESD}	IEC 61000-4-2 (Air Discharge)	±15			kV
Line Capacitance ^{1, 2}	C_{L}	Reverse Bias=0V, f=3GHz		0.2		pF

Note 1: Parameter is guaranteed by design and/or component characterization.

8/20µs Pulse Waveform



Clamping Voltage vs I_{PP}



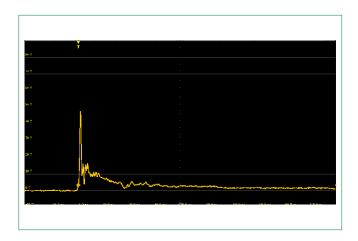


Note 2: Test equipment accuracy ±50fF.

Note 3: Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2= 90ns

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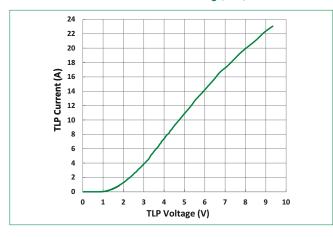
IEC 61000-4-2 +8 kV Contact ESD Clamping Voltage



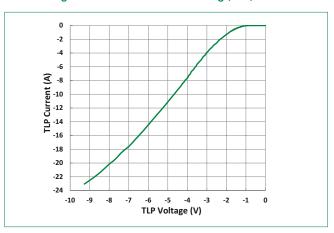
IEC 61000-4-2 -8 kV Contact ESD Clamping Voltage



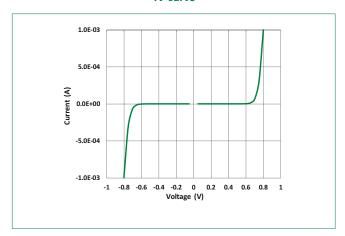
Positive Transmission Line Pulsing (TLP) Plot



Negative Transmission Line Pulsing (TLP) Plot



IV curve



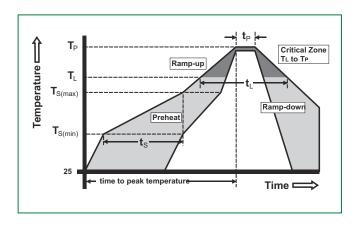


Soldering Parameters

Reflow Co	ndition	Pb – Free assembly	
	- Temperature Min (T _{s(min)})	150°C	
Pre Heat	- Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 - 120 secs	
Average ra	amp up rate (Liquidus) Temp k	3°C/second max	
$T_{S(max)}$ to T_{L}	- Ramp-up Rate	3°C/second max	
Reflow	- Temperature (T _L) (Liquidus)	217°C	
	- Temperature (t _L)	60 - 150 seconds	
Peak Temp	erature (T _P)	260 ^{+0/-5} °C	
Time with Temperatu	in 5°C of actual peak ıre (t _p)	30 seconds	
Ramp-dov	vn Rate	6°C/second max	
Time 25°C	to peak Temperature (T _P)	8 minutes Max.	
Do not exc	ceed	260°C	

Ordering Information

Part Number	Package	Min. Order Qty.
SP00R6-01WTG	Flipchip	10000



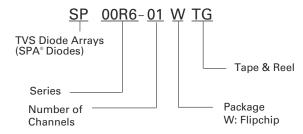
Product Characteristics

Lead Plating	Tin plating
Lead material	Copper bump
Substrate Material	Silicon
Flammability	UL Recognized compound meeting flammability rating V-0

Part Marking System



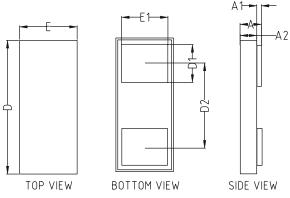
Part Numbering System





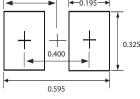
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Package Dimensions — FLIPCHIP



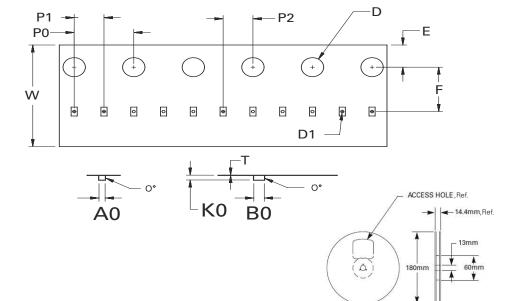
BOTTOM VIEW	SIDE VIEW
0.298	

	0201 Flipchip				
Symbol	mbol Millimete		ters Inches		
	Min	Max	Min	Max	
D	0.605	0.655	0.0238	0.0258	
E	0.305	0.355	0.0120	0.0140	
D1	0.145	0.155	0.0057	0.0061	
E1	0.245	0.255	0.0096	0.0100	
D2	0.400 BSC		0.015	7 BSC	
Α	0.273	0.329	0.0107	0.0130	
A2	0.265	0.315	0.0104	0.0124	
A1	0.008	0.014	0.0003	0.0006	



Recommended Soldering Pad Layout (mm)

Embossed Carrier Tape & Reel Specification — FLIPCHIP



Symbol	Millimeters
A0	0.41+/-0.03
В0	0.70+/-0.03
D	ø 1.50 + 0.10
D1	ø 0.20 +/- 0.05
E	1.75+/-0.10
F	3.50+/-0.05
K0	0.38+/-0.03
P0	4.00+/-0.10
P1	2.00+/-0.05
P2	2.00+/-0.05
W	8.00+0.30/-0.10
Т	0.23+/-0.02

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8mm TAPE AND REEL

